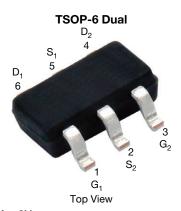


Vishay Siliconix

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



Marking code: 8X

PRODUCT SUMMARY						
V _{DS} (V)	-30					
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	-0.110					
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	-0.185					
I _D (A)	-2.75					
Configuration	Dual					
Package	TSOP-6					

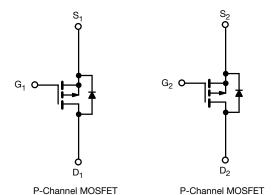
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912









ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-30	V		
Gate-source voltage	V _{GS}	± 20				
Continuous drain current (T, ₁ = 150 °C) ^a	T _C = 25 °C	- I _D	-3	- A		
Continuous drain current (1 _J = 150 °C) ^a	T _C = 125 °C		-1.74			
Pulsed drain current		I _{DM}	-11	A		
Continuous source current (diode conduction) a	I _S	-2.1				
Maximum power dissipation ^a	T _C = 25 °C	P _D	1.67	W		
	T _C = 125 °C		0.56	VV		
Unclamped inductive surge UIS		I _{AV}	-5	Α		
Operating junction and storage temperature range	е	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Maximum junction-to-ambient ^a	Steady state	R_{thJA}	150	°C/W		
Maximum junction-to-foot (drain)	Steady state	R_{thJF}	90	C/VV		

Note

a. Surface mounted on 1" x 1" FR4 board



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		-1.5	-	-2.5	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1	μA
current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	-50	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-4	-	-	Α
Drain-source on-state	В	$V_{GS} = -10 \text{ V}$	I _D = -1.5 A	-	0.085	0.133	
resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -2 A	-	0.135	0.185	Ω
Forward transconductance a	9 _{fs}	V _I	_{DS} = -5 V, I _D = -1 A	-	4.2	-	S
Diode forward voltage a	V_{SD}	Is	= -0.5 A, V _{GS} = 0 V	-	-0.83	-1.10	V
Dynamic ^b							
Input capacitance	C _{iss}			-	456	570	
Output capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V}$	-	85	106	pF
Reverse capacitance	C _{rss}			-	59	74	1
Total gate charge	Q_g			-	9.7	12.2	
Gate-source charge	Q _{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -15 \text{ V}, I_D = -3 \text{ A}$	-	1.3	-	nC
Gate-drain charge	Q_{gd}			-	2	-	
Gate resistance	R_g	f = 1 MHz		9	-	24	Ω
Turn-on delay time	t _{d(on)}			-	6.6	8.3	
Rise time	t _r	V_{DD} = -10 V, R_L = 10 Ω , $I_D \cong$ -1 A, V_{GEN} = -10 V, R_g = 1 Ω		-	2.4	3	1
Turn-off delay time	t _{d(off)}			-	18.4	23	ns ns
Fall time	t _f			-	2.2	2.8	
Source-Drain Diode Ratings	and Charac	teristic ^b		•		•	
Pulsed current	I _{SM}			-	-	-11	Α
Forward voltage	V_{SD}	I _F = 0.5 A, V _{GS} = 0 V		-	-0.83	-1.1	V
Reverse recovery fall time	ta			-	9.1	-	ns
Reverse recovery rise time	t _b	V_{DD} = -24 V, I_{FM} = -1.5 A, di/dt = 100 A/μs, R = 160 Ω , L = 1 mH, pulse W = 2 μs		-	4.8	-	ns
Body diode reverse recovery time	t _{rr}			-	14	28	ns
Body diode reverse recovery charge	Q _{rr}			-	9	18	μC
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.4	-	Α

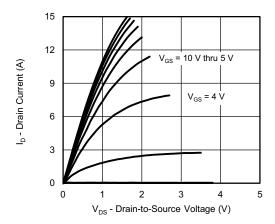
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

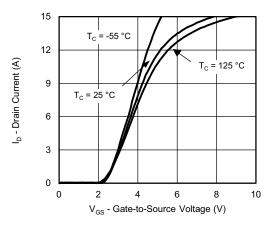
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



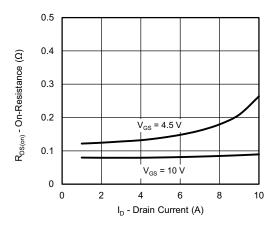
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



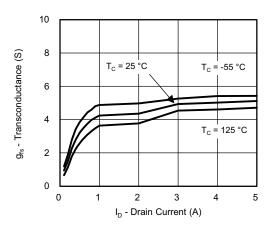
Output Characteristics



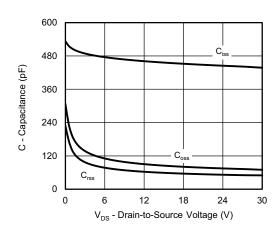
Transfer Characteristics



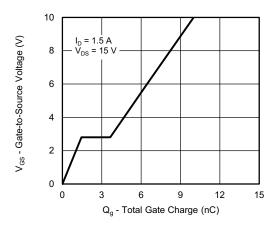
On-Resistance vs. Drain Current



Transconductance



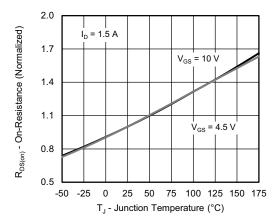
Capacitance



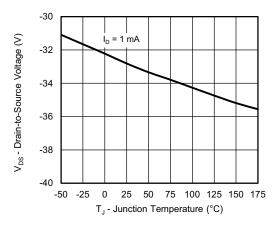
Gate Charge



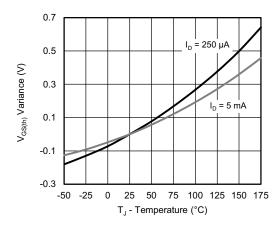
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



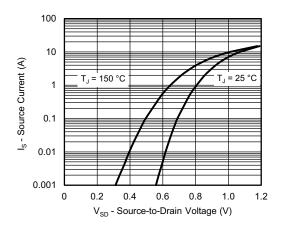
On-Resistance vs. Junction Temperature



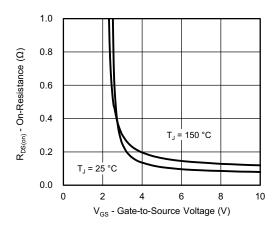
Drain Source Breakdown vs. Junction Temperature



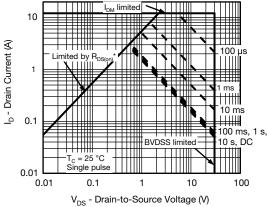
Threshold Voltage



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

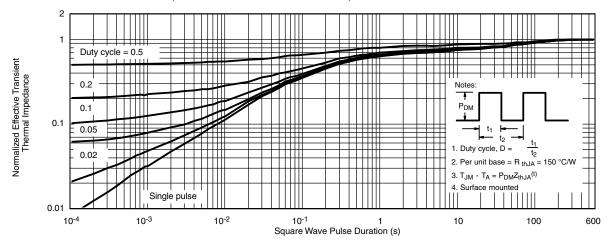


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

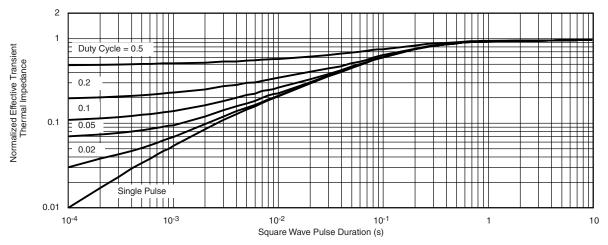
Safe Operating Area, Junction-to-Case



TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

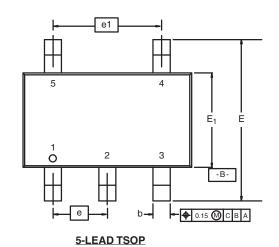
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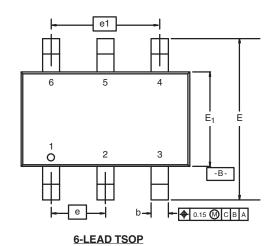


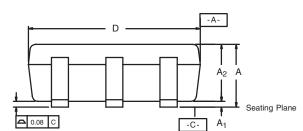


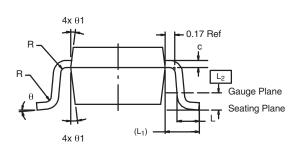
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C









	MIL	LIMETER	RS	INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071 0.075		0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref				0.024 Ref	
L ₂	0.25 BSC				0.010 BSC	
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom				7° Nom	
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

Document Number: 71200 www.vishay.com 18-Dec-06



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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